

N-Channel Super Junction Power MOSFET III

General Description

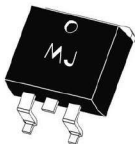
The series of devices use advanced super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

Features

- ◆ New technology for high voltage device
- ◆ Low on-resistance and low conduction losses
- ◆ Small package
- ◆ Ultra Low Gate Charge cause lower driving requirements
- ◆ 100% Avalanche Tested
- ◆ ROHS compliant



Schematic diagram



TO-263

Application

- ◆ Power factor correction (PFC)
- ◆ Switched mode power supplies(SMPS)
- ◆ Uninterruptible Power Supply (UPS)

V_{DS}	650	V
$R_{DS(ON)TYP}$	290	mΩ
I_D	11.5	A

Package Marking And Ordering Information

Device	Device Package	Marking
MJ65T360D	TO-263	MJ65T360D

Table 1. Absolute Maximum Ratings (Tc=25°C)

Parameter	Symbol	MJ65T360D	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	650	V
Gate-Source Voltage ($V_{DS}=0V$) AC ($f>1\text{ Hz}$)	V_{GS}	±30	V
Continuous Drain Current at $T_c=25^{\circ}C$	I_D (DC)	11.5	A
Continuous Drain Current at $T_c=100^{\circ}C$	I_D (DC)	7	A
Pulsed drain current ^(Note 1)	I_{DM} (pluse)	46	A
Maximum Power Dissipation ($T_c=25^{\circ}C$)	P_D	101	W
Derate above 25°C	P_D	0.81	W/°C
Single pulse avalanche energy ^(Note 2)	E_{AS}	144	mJ
Avalanche current ^(Note 1)	I_{AR}	6	A
Repetitive Avalanche energy, t_{AR} limited by T_{jmax} ^(Note 1)	E_{AR}	0.5	mJ

Parameter	Symbol	MJ65T360D	Unit
Drain Source voltage slope, $V_{DS} \leq 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS} \leq 480\text{ V}, I_{SD} < I_D$	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+150	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	MJ65T360D	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R _{thJC}	1.24	°C/W
Thermal Resistance, Junction-to-Ambient (Maximum)	R _{thJA}	62	°C/W

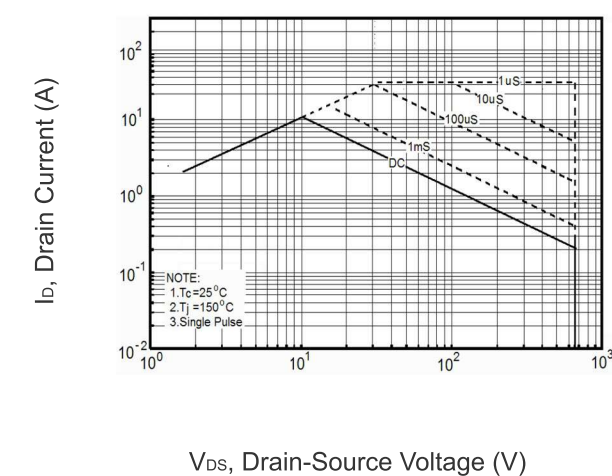
Table 3. Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	650	-	-	V
Zero Gate Voltage Drain Current (Tc=25°C)	I _{DSS}	V _{DS} =650V,V _{GS} =0V	-	0.05	1	μA
Zero Gate Voltage Drain Current (Tc=125°C)	I _{DSS}	V _{DS} =650V,V _{GS} =0V	-	-	100	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	3	3.5	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V,I _D =7A	-	290	360	mΩ
Dynamic Characteristics						
Input Capacitance	C _{ies}	V _{DS} =50V,V _{GS} =0V F=1.0MHz	-	870	-	PF
Output Capacitance	C _{OSS}		-	54	-	PF
Reverse Transfer Capacitance	C _{rss}		-	1.8	-	PF
Total Gate Charge	Q _g	V _{DS} =480V,I _D =11.5A V _{GS} =10V	-	19	-	nC
Gate-Source Charge	Q _{gs}		-	6	-	nC
Gate-Drain Charge	Q _{gd}		-	6.5	-	nC
Switching times						
Turn-on Delay Time	t _{d(on)}	V _{DD} =380V,I _D =5.5A R _G =3Ω,V _{GS} =10V	-	11	-	nS
Turn-on Rise Time	t _r		-	8	-	nS
Turn-Off Delay Time	t _{d(off)}		-	58	70	nS
Turn-Off Fall Time	t _f		-	9	14	nS
Source- Drain Diode Characteristics						
Source-drain current (Body Diode)	I _{SD}	T _C =25°C	-	-	11.5	A
Pulsed Source-drain current (Body Diode)	I _{SDM}		-	-	46	A
Forward On Voltage	V _{SD}	T _J =25°C,I _{SD} =11.5A,V _{GS} =0V	-	0.9	1.2	V
Reverse Recovery Time	t _{rr}	T _J =25°C,I _F =5.8A di/dt=100A/μs	-	220	-	nS
Reverse Recovery Charge	Q _{rr}		-	2.2	-	uC
Peak reverse recovery Current	I _{rrm}		-	19	-	A

Notes

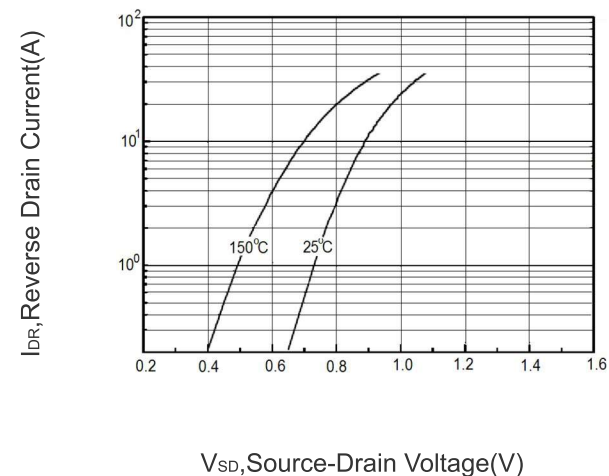
- 1.Repetitive Rating: Pulse width limited by maximum junction temperature
- 2.Tj=25℃,VDD=50V,VG=10V, RG=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)



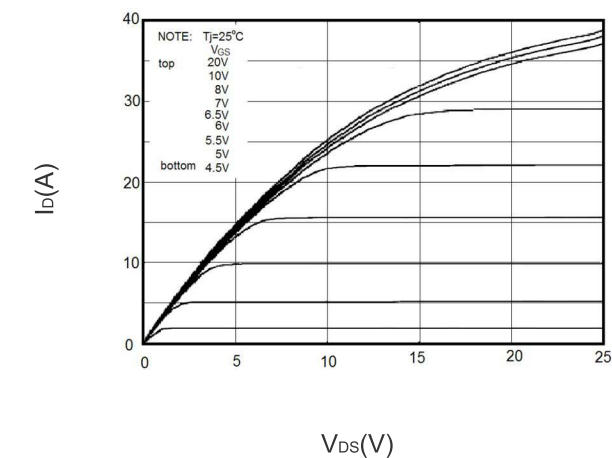
V_{DS}, Drain-Source Voltage (V)

Figure 1 Safe operating area



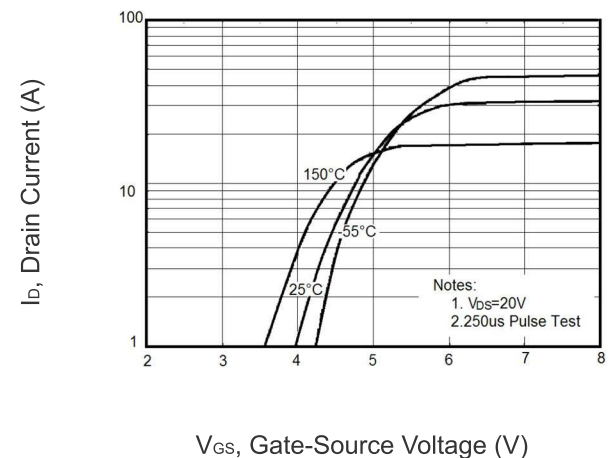
V_{SD},Source-Drain Voltage(V)

Figure 2 Source-Drain Diode Forward Voltage



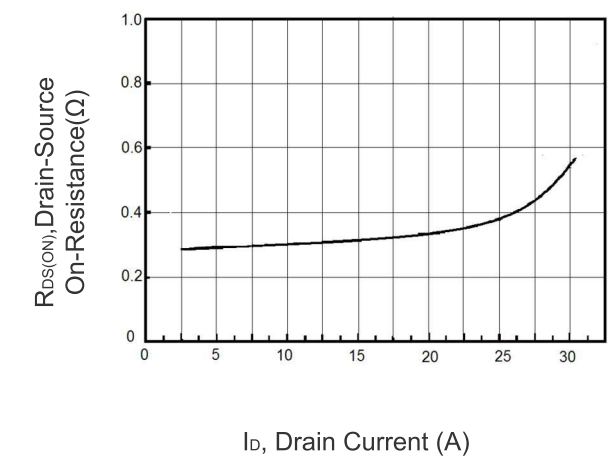
V_{DS}(V)

Figure 3 Output characteristics



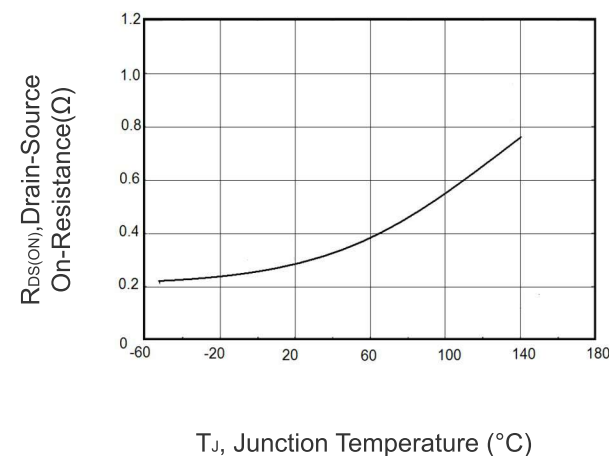
V_{GS}, Gate-Source Voltage (V)

Figure 4 Transfer characteristics



ID, Drain Current (A)

Figure 5 Static drain-source on resistance



T_J, Junction Temperature (°C)

Figure 6 R_{DS(ON)} vs Junction Temperature

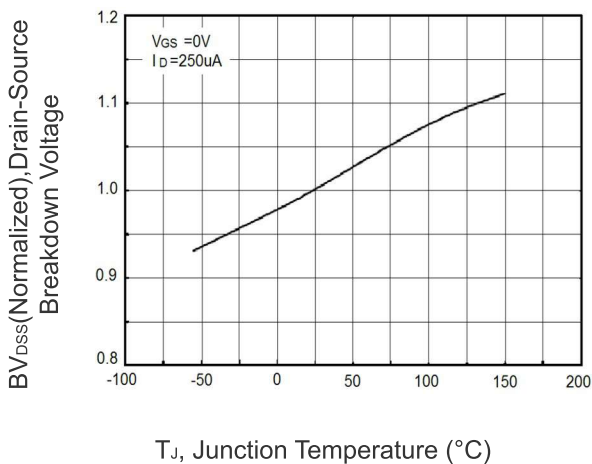


Figure 7 BV_{DSS} vs Junction Temperature

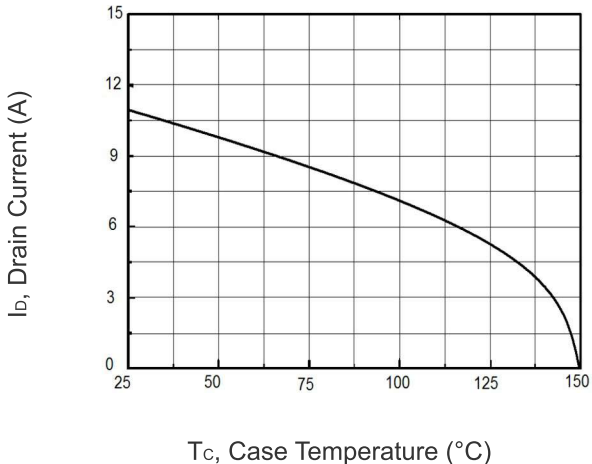


Figure 8 Maximum I_D vs Junction Temperature

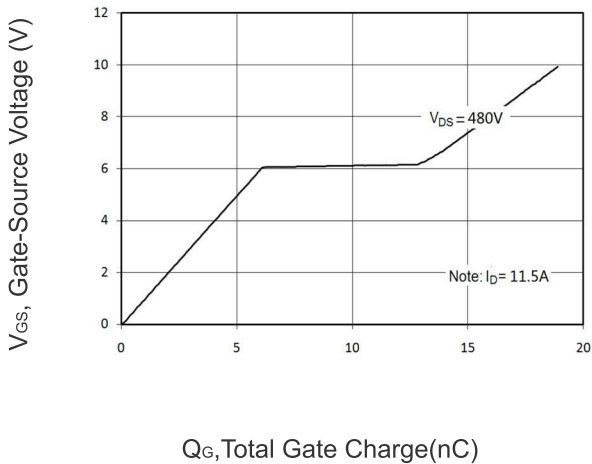


Figure 9 Gate charge waveforms

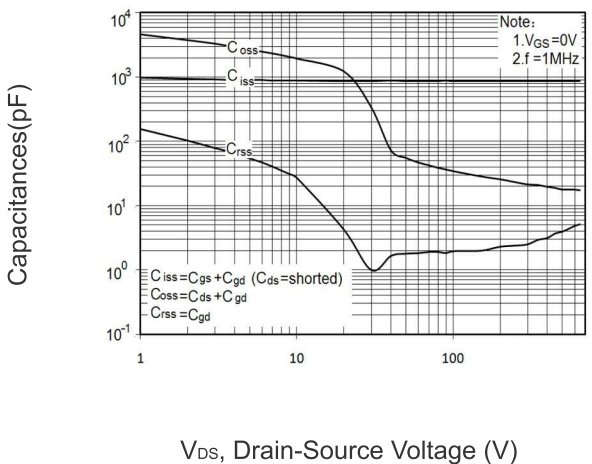


Figure 10 Capacitance

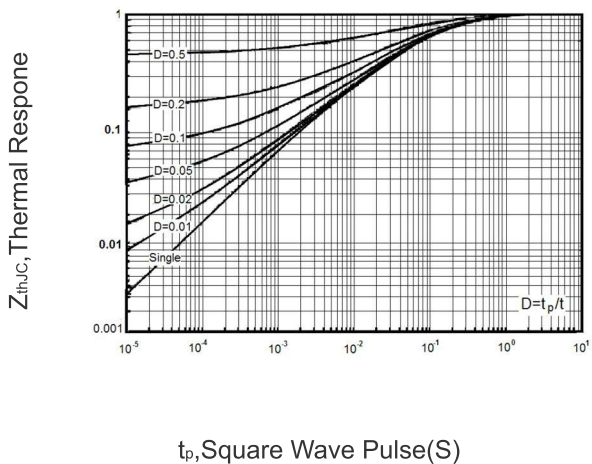


Figure 11 Transient Thermal Impedance

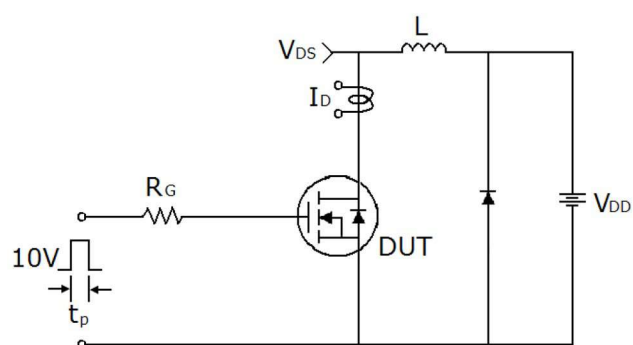
Test circuit



Gate charge test circuit & Waveform

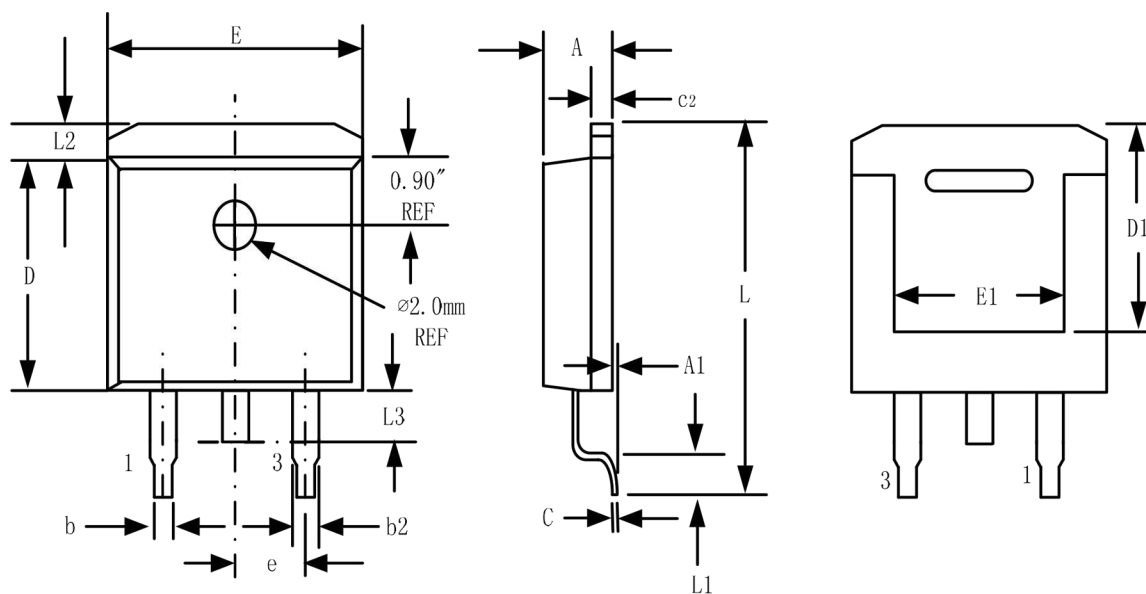


Switch Time Test Circuit



Unclamped Inductive Switching Test Circuit & Waveforms

TO-263-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.57	0.170	0.180
A1	-	0.25		0.010
b	0.71	0.94	0.028	0.037
b2	1.15	1.40	0.045	0.055
c	0.46	0.61	0.018	0.024
c2	1.22	1.40	0.048	0.055
D	8.89	9.40	0.350	0.370
D1	8.01	8.23	0.315	0.324
E	10.04	10.28	0.395	0.405
E1	7.88	8.08	0.310	0.318
e	2.54 BSC		0.100 BSC	
L	14.73	15.75	0.580	0.620
L1	2.29	2.79	0.090	0.110
L2	1.15	1.39	0.045	0.055
L3	1.27	1.77	0.050	0.070

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